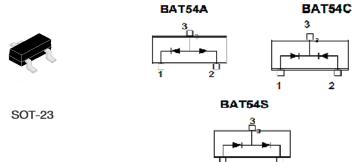


An IATF 16949, ISO9001 and ISO 14001/ISO 45001 Certified Company





SILICON PLANAR SCHOTTKY DIODES



BAT54A BAT54C BAT54S

SOT-23 SMD Package RoHS compliant

Marking

BAT54A = **L42** BAT54C = **L43** BAT54S = **L44**

APPLICATION: Ultra High Speed Switching Diodes

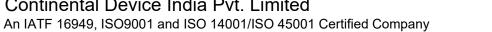
ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Forward Current (DC)	I _F	200	mA
Repetitive Peak Forward Current	I _{FRM}	300	mA
Non Repetitive Peak Forward Current t<1s	I _{FSM}	600	mA
Power Dissipation T _a =25°C	P _D	230	mW
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	T _i	125	°C

Thermal Resistance

Junction	to Ambient in free air, Mounted	В	430	12/\Δ/	Ī
on a Cer	ramic Substrate of 10mm x 8mm x 0.6mm	rt _{th (j-a)}	430	K/W	









ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	VALUE			UNIT	
PARAMETER	STWIBUL	TEST CONDITION	MIN	TYP	MAX	UNIT	
		I _F =0.1mA			0.24	V	
	V _F	I _F = 1mA			0.32	V	
Forward Voltage		I _F = 10mA		1	0.40	V	
		$I_F = 30 \text{mA}$		1	0.50	V	
		I _F = 100mA		-	0.80	V	
Reverse Current	I _R	V _R =25V		-	2.0	μΑ	
Reverse Breakdown Voltage	$V_{(BR)}$	I _R =100μA	30	-	-	V	
DYNAMIC CHARACTERISTICS							
Diode Capacitance	C _d	V _R =1V, f=1MHz		1	10	pF	
Reverse Recovery Time	t _{rr}	When Switched from I_F =10mA to I_R =10mA, measured at I_{RR} =1mA, R_L =100 Ω		1	5	ns	



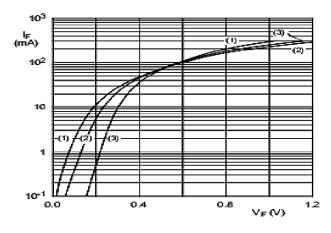






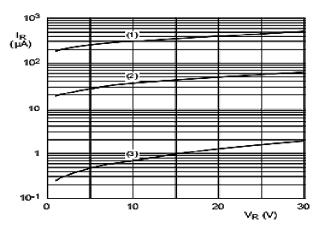
TYPICAL CHARACTERISTIC CURVES

Fig 1: Forward current as a function of forward voltage; typical values



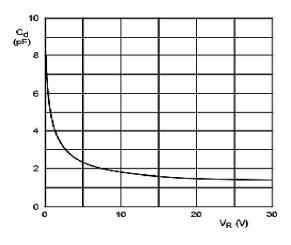
- (1) T_{omb} = 125 °C
- (2) T_{amb} = 85 °C
- (3) T_{amb} = 25 °C

Fig 2: Reverse current as a function of reverse voltage; typical values



- (1) T_{amb} = 125 °C
- (2) T_{amb} = 85 °C
- (3) T_{amb} = 25 °C

Fig 3: Diode capacitance as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

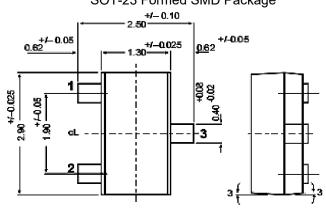


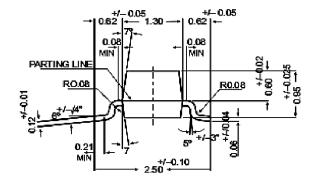




PACKAGE DETAILS

SOT-23 Formed SMD Package





All dimensions are in mm

BAT54A Pin Configuration

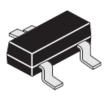
- 1. CATHODE
- 2. CATHODE
- 3. ANODE

BAT54C Pin Configuration

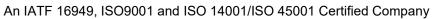
- 1. ANODE
- 2. ANODE
- 3. CATHODE

BAT54S Pin Configuration

- 1. ANODE
- 2. CATHODE
- 3. ANODE / CATHODE



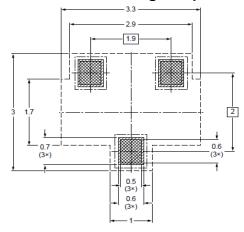






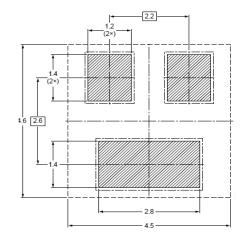


Recommended Reflow soldering footprint



solder lands
solder resist
solder paste
occupied area
Dimensions in mm

Recommended Wave soldering footprint



solder lands
solder resist
current occupied area
Dimensions in mm



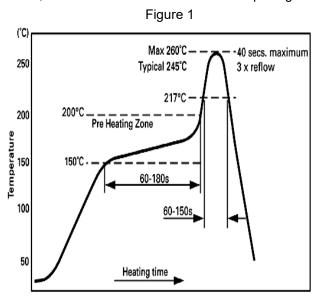


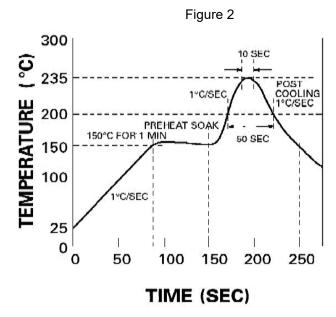
Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.





Reflow profiles in tabular form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat		
Time maintained above: – Temperature – Tim	200°C 30-50 seconds	217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max



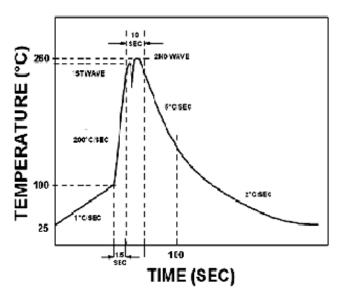


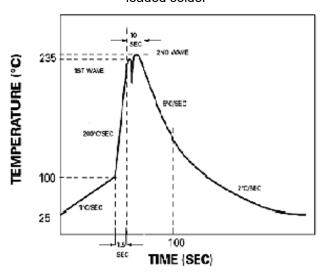


Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pbfree terminal plating where a Pb-free solder is used

The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder





Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-free System	
Average Ramp-Up Rate	~200°C/second	~200°C/second	
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec	
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp	
Peak Temperature	235°C	260°C max.	
Time within +0 -5°C of actual Peak	10 seconds	10 seconds	
Ramp-Down Rate	5°C/second max.	5°C/second max.	





Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level		
Level	Time	Condition
1	Unlimited	≤30 °C / 85% RH
2	1 Year	≤30 °C / 60% RH
2a	4 Weeks	≤30 °C / 60% RH
3	168 Hours	≤30 °C / 60% RH
4	72 Hours	≤30 °C / 60% RH
5	48 Hours	≤30 °C / 60% RH
5a	24 Hours	≤30 °C / 60% RH
6	Time on Label(TOL)	≤30 °C / 60% RH





Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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